





**TUSB216I** JAJSLB7A - MARCH 2021 - REVISED DECEMBER 2023

# TUSB216I USB 2.0 高速シグナル・コンディショナ、BC 1.2 コントローラ付き

## 1 特長

- 広い電源電圧範囲:2.3~6.5V
- USB 切断時およびシャットダウン時の非常に低い消費
- USB 2.0 High Speed 信号のコンディショニングを提
- USB 2.0、OTG 2.0、BC 1.2 に対応
- Low-Speed、Full-Speed、High-Speed 信号処理の
- BC 1.2 CDP バッテリ充電コントローラを内蔵
- 特定のホストやデバイスに非依存
- 最大 5m のケーブルをサポート
  - 外付けのプルダウン抵抗により4つの信号ブースト (エッジ・ブーストと DC ブースト) 設定を選択可能
  - プルアップまたはプルダウンで選択可能な3つの RX 感度設定により、損失が大きいアプリケーション の ISI ジッタを補償
- 2 つの TUSB216I デバイスを使って最大 10m のケー ブル長に対応
- スケーラブルなソリューション 損失が大きいアプリケ ーションに対応するため、デバイスをデイジー・チェー
- TUSB211A、212、214、217A (3.3V) とピン互換

# 2 アプリケーション

- ラップトップ、デスクトップまたはドッキング・ステーション
- 携帯電子機器
- タブレット
- 携帯電話
- ・ テレビ
- アクティブ・ケーブル、延長ケーブル、バックプレーン

# 3 概要

TUSB216I は第3世代 USB 2.0 High Speed 信号コン ディショナーで、伝送チャネルでの AC 損失 (容量性負荷 による) および DC 損失 (抵抗損失による) を補償するよう に設計されています。

TUSB216I には、エッジ・ブースタにより USB 2.0 High Speed 信号の遷移エッジを高速化し、DC ブースト機能に より静的電圧レベルを上げる特許取得済みの設計が採用 されています。

また、TUSB216I はプリイコライゼーション機能を備えてい るため、レシーバ感度を高め、長いケーブルを使用するア プリケーションで ISI (符号間干渉) ジッタを補償できます。 USB Low Speed および Full Speed 信号特性は、 TUSB216I による影響を受けません。

TUSB216I は、パケット・タイミングを変更せず、また、伝 搬遅延やレイテンシを追加せずに、信号品質を向上させ ることができます。

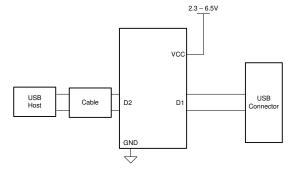
TUSB216I により、最長 5 メートルのケーブルを使用した システムで、USB 2.0 High Speed 近端アイ・コンプライア ンスに合格することが可能になります。

TUSB216I は USB On-The-Go (OTG) および Battery Charging (BC 1.2) プロトコルにも対応しています。 内蔵 の BC 1.2 バッテリ充電コントローラは、制御ピンを使って 有効化できます。

#### 製品情報

部品番号(1)	パッケージ <sup>(2)</sup>	動作温度 (T <sub>A</sub> ) ℃	パッケージ サイズ (3)
TUSB216		0~70	
TUSB216I	RWB (X2QFN、12)	-40~85	1.6mm × 1.6mm
TUSB216-Q1		-40~105	

- (1) 製品比較表を参照してください。
- 詳細については、セクション 11 を参照してください。 (2)
- パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピ ンも含まれます。



概略回路図



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# **4 Device Comparison**

	TUSB211A	TUSB212	TUSB214	TUSB216	TUSB217A
Industrial Variant Available	Υ	Υ	Υ	Υ	Υ
Automotive Variant Available	Υ	Υ	Υ	Υ	Υ
Supply (V)	2.3 to 6.5	3.3	3.3	2.3 to 6.5	2.3 to 6.5
DC Boost	Tandem with AC Boost	3 levels	3 levels	Tandem with AC Boost	Tandem with AC Boost
I2C Control	N	Υ	Υ	Υ	Υ
RX pre-equalization for ISI compensation	N/A	N/A	N/A	3 levels	3 levels
Charging Downstream Port (CDP) controller	N/A	N/A	Always ON	Pin Controlled	Always ON. Dynamically selected by DCP/CDP pin
Dedicated Charging Port (DCP) controller	N/A	N/A	N/A	N/A	Always ON. Dynamically selected by DCP/CDP pin
Cable length compensation for near- end high-speed eye mask Compliance (pre-channel before redriver/post- channel after redriver) (meter - gauge)	6/3 - 28AWG (10 - 24AWG with one redriver on each end)	4/2 - 28AWG	4/2 - 28AWG	6/3 - 28AWG (10 - 24AWG with one redriver on each end)	6/3 - 28AWG (10 - 24AWG with one redriver on each end)
Cable length compensation for far-end high-speed eye mask Compliance (pre-channel before redriver/post-channel after redriver) (meter - gauge)	10/8 - 26AWG (10 - 28AWG with one redriver on each end)	8/6 - 28AWG	8/6 - 28AWG	10/8 - 26AWG (10 - 28AWG with one redriver on each end)	10/8 - 26AWG (10 - 28AWG with one redriver on each end)

Product Folder Links: TUSB216I



# **5 Pin Configuration and Functions**

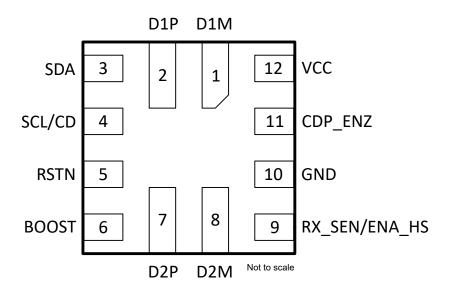


図 5-1. TUSB216I RWB Package, 12-Pin X2QFN (Top View)

表 5-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	INTERNAL	DESCRIPTION		
NAME NO. PULLUP/PULLDOWN	DESCRIPTION					
BOOST	6	I	N/A	USB High-speed boost select via external pull down resistor. Both edge boost and DC boost are controlled by a single pin in non-I2C mode. In I2C mode edge boost and DC boost can be individually controlled. Sampled upon power up. Does not recognize real time adjustments. Auto selects BOOST LEVEL = 3 when left floating.		
CDP_ENZ	11	1	500 kΩ PU	Set CDP_ENZ is low to enable BC 1.2 CDP controller		
RX_SEN <sup>(3)</sup> /ENA_HS	9	l/O	N/A	In I2C mode: Reserved for TI test purpose. In non-I2C mode: At reset: 3-level input signal RX_SEN. USB High-speed RX Sensitivity Setting to Compensate ISI Jitter H (pin is pulled high) – high RX sensitivity (high loss channel) M (pin is left floating) – medium RX sensitivity (medium loss channel) L (pin is pulled low) – low RX sensitivity (low loss channel) After reset: Output signal ENA_HS. Flag indicating that channel is in High-speed mode. Asserted upon: 1. Detection of USB-IF High-speed test fixture from an unconnected state followed by transmission of USB TEST_PACKET pattern. 2. Squelch detection following USB reset with a successful HS handshake [HS handshake is declared to be successful after single chirp J chirp K pair where each chirp is within 18 µs – 128 µs].		



### 表 5-1. Pin Functions (続き)

PIN		TYPE <sup>(1)</sup>	INTERNAL	DESCRIPTION	
NAME	NO.	ITPE''	PULLUP/PULLDOWN	DESCRIPTION	
D2P	7	I/O	PULLUP/PULLDOWN         N/A       USB High-speed positive port.         N/A       USB High-speed negative port.         N/A       USB High-speed negative port.         N/A       USB High-speed positive port.         I2C Mode:       Bidirectional I2C data pin [7-bit I2C slave address = 0x2C]. In non I2C mode: Reserved for TI test purpose.         N/A       Supply power         Device disable/enable. Low – Device is at reset and in shutdown, and High - Normal operation. Recommend 0.1-μF external capacitor to GND to ensure cl power on reset if not driven. If the pin is driven, it must be huntil the supply voltage for the device reaches within specifing I2C address = 0x2C].		
D2M	8	I/O	N/A	USB High-speed negative port.	
GND	10	Р	PULLUP/PULLDOWN         N/A       USB High-speed positive port.         N/A       USB High-speed negative port.         N/A       USB High-speed negative port.         N/A       USB High-speed positive port.         I2C Mode:       Bidirectional I2C data pin [7-bit I2C slave address = 0x2C]. In non I2C mode:         Reserved for TI test purpose.         N/A       Supply power         Device disable/enable.       Low – Device is at reset and in shutdown, and High - Normal operation.         Recommend 0.1-μF external capacitor to GND to ensure cle power on reset if not driven. If the pin is driven, it must be huntil the supply voltage for the device reaches within specified in I2C mode:         When RSTN asserted there is a 500 kQ PD       In I2C mode:         When RSTN asserted there is a 500 kQ PD       After reset: Output CD. Flag indicating that a USB device is		
D1M	1	I/O	N/A	USB High-speed negative port	
D1P	2	I/O	N/A	USB High-speed positive port.	
SDA <sup>(2)</sup>	3	I/O		Bidirectional I2C data pin [7-bit I2C slave address = 0x2C]. In non I2C mode:	
VCC	12	Р	N/A	Supply power	
RSTN	5	I		Low – Device is at reset and in shutdown, and	
SCL <sup>(2)</sup> /CD	4	I/O		I2C clock pin [I2C address = 0x2C].	

- (1) I = input, O = output, P = power
- (2) Pull-up resistors for SDA and SCL pins in I<sup>2</sup>C mode should be R<sub>Pull-up</sub> (depending on I2C bus voltage). If both SDA and SCL are pulled up at power-up the device enters into I<sup>2</sup>C mode.
- (3) Pull-down and pull-up resistors for RX\_SEN pin must follow  $R_{RXSEN1}$  and  $R_{RXSEN2}$  resistor recommendations in non I<sup>2</sup>C mode.

### **6 Specifications**

### 6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
Supply voltage range	VCC	-0.3	7	V
Voltage range USB data	DxP, DxM	-0.3	5.5	V
Voltage range on BOOST pin	BOOST	-0.3	1.98	V
Voltage range other pins	RX_SEN, CDP_ENZ, SDA, SCL, RSTN	-0.3	5.5	V
Storage temperature, T <sub>stg</sub>		-65	150	°C
Maximum junction temperature, T	J (max)		125	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

### 6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
V <sub>(ESD)</sub>	Liectiostatic discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±750	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

# **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage	2.3	5	6.5	V
T <sub>A</sub>	Operating free-air temperature (Industrial)	-40		85	°C
T <sub>J</sub>	Junction temperature (Industrial)			105	°C
V <sub>I2C_BUS</sub>	I2C Bus Voltage	1.62		3.6	V
DxP, DxM	Voltage range USB data	0		3.6	V
BOOST	Voltage range BOOST pin	0		1.98	V
DIGITAL	Voltage range other pins (SCL, SDA, RSTN, CDP_ENZ)	0		3.6	V
RX_SEN	Voltage range RX_SEN pin	0		5.0	V

#### 6.4 Thermal Information

	THERMAL METRIC (1)	RWB (X2QFN)	UNIT
	I DERWAL METRIC (1)	12 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	137.4	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	62	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	67.2	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.9	°C/W
ΨЈВ	Junction-to-board characterization parameter	67.3	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

Product Folder Links: TUSB216I

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## **6.5 Electrical Characteristics**

Over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
POWER						
I <sub>ACTIVE_HS</sub>	High Speed Active Current	USB channel = HS mode. 480 Mbps traffic. V <sub>CC</sub> supply stable, with Boost = Max		22	36	mA
I <sub>IDLE_HS</sub>	High Speed Idle Current	USB channel = HS mode, no traffic.  V <sub>CC</sub> supply stable, Boost = Max		22	36	mA
I <sub>HS_SUPSPEND</sub>	High Speed Suspend Current	USB channel = HS Suspend mode. V <sub>CC</sub> supply stable		0.75	1.4	mA
I <sub>FS</sub>	Full-Speed Current	USB channel = FS mode, 12 Mbps traffic, V <sub>cc</sub> supply stable		0.75	1.4	mA
I <sub>DISCONN</sub>	Disconnect Power	Host side application. No device attachment.		0.80	1.4	mA
I <sub>SHUTDN</sub>	Shutdown Power	RSTN driven low, V <sub>CC</sub> supply stable		60	115	μA
CONTROL PIN LE	EAKAGE				<u> </u>	
I <sub>LKG_FS</sub>	Pin failsafe leakage current for SDA, RSTN	V <sub>CC</sub> = 0 V, pin at V <sub>IH, max</sub>		10	15	μA
I <sub>LKG_FS</sub>	Pin failsafe leakage current for RX_SEN	V <sub>CC</sub> = 0 V, pin at V <sub>IH, max</sub>		6	15	μA
I <sub>LKG_FS</sub>	Pin failsafe leakage current for SCL	V <sub>CC</sub> = 0 V, pin at V <sub>IH, max</sub>			70	nA
INPUT RSTN		,	,			
V <sub>IH</sub>	High level input voltage		1.5		3.6	V
V <sub>IL</sub>	Low-level input voltage		0		0.5	V
I <sub>IH</sub>	High level input current	V <sub>IH</sub> = 3.6 V, R <sub>PU</sub> enabled			±15	μA
I <sub>IL</sub>	Low level input current	V <sub>IL</sub> = 0V, R <sub>PU</sub> enabled			±20	μA
INPUT DIGITAL						
V <sub>IH</sub>	High level input voltage (CDP_ENZ)		1.5		3.6	V
V <sub>IL</sub>	Low-level input voltage (CDP_ENZ)		0		0.5	V
I <sub>IL</sub>	Low level input current	V <sub>IL</sub> = 0V			±20	μA
I <sub>IH</sub>	High level input current	V <sub>IH</sub> = 3.6 V			±15	μA
INPUT RX_SEN (	3-level input, for mid level leave pin f	loating)				
V <sub>IH(Max)</sub>	Maximum High level input voltage	VCC = 2.3V to 6.5V			5.0	V
		VCC > 4.5V	3.3			V
$V_{IH(Min)}$	Minimum High level input voltage	VCC = 2.3V to 4.5V (% of VCC)	75			%
	1 1 1	VCC > 4.5V			0.75	V
$V_{IL}$	Low level input voltage	VCC = 2.3V to 4.5V (% of VCC)			15	%
INPUT BOOST	I	1				
R <sub>BOOST_LVL0</sub>	External pulldown resistor for BOOST Level 0				160	Ω
R <sub>BOOST_LVL1</sub>	External pulldown resistor for BOOST Level 1		1.5	1.8	2	kΩ
R <sub>BOOST_LVL2</sub>	External pulldown resistor for BOOST Level 2		3.4	3.6	3.96	kΩ
R <sub>BOOST_LVL3</sub>	External pulldown resistor for BOOST Level 3 to remove upper limit for resistor value, can be left open		7.5			kΩ
OUTPUTS CD, EN	NA_HS					
V <sub>OH</sub>	High level output voltage for CD and ENA_HS	I <sub>O</sub> = -50 μA, VCC >= 3.0V	2.5			V
V <sub>OH</sub>	High level output voltage for CD	I <sub>O</sub> = -25 μA, VCC = 2.3V	1.7			V

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English Data Sheet: SLLSFM9

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Product Folder Links: TUSB216I



# 6.5 Electrical Characteristics (続き)

Over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
V <sub>OH</sub>	High level output voltage for ENA_HS	I <sub>O</sub> = -25 μA, VCC = 2.3V	1.8			V
V <sub>OL</sub>	Low level output voltage for CD and ENA_HS	Ι <sub>Ο</sub> = 50 μΑ			0.3	V
I2C						
C <sub>I2C_BUS</sub>	I <sup>2</sup> C Bus Capacitance		4		150	pF
I <sub>OL</sub>	I <sup>2</sup> C open drain output current	V <sub>OL</sub> = 0.4V	1.5			mA
V <sub>IL</sub>	2.3V<= VCC<= 4.3V, V <sub>I2C_BUS</sub> = 1.8V +/-10%	$R_{Pull-up}$ =1.6kΩ to 2.5kΩ, % of $V_{I2C\_BUS}$			25	%
V <sub>IL</sub>	V <sub>I2C_BUS</sub> = 3.3V +/-10%	$R_{Pull-up}$ =2.8kΩ to 7kΩ, % of $V_{I2C\_BUS}$			25	%
V <sub>IH</sub>	2.3V<= VCC<= 4.3V, V <sub>I2C_BUS</sub> = 1.8V +/-10%	$R_{Pull-up}$ =1.6kΩ to 2.5kΩ, % of $V_{I2C\_BUS}$	80			%
V <sub>IH</sub>	V <sub>I2C_BUS</sub> = 3.3V +/-10%	$R_{Pull-up}$ =2.8kΩ to 7kΩ, % of $V_{I2C\_BUS}$	75			%
R <sub>Pull-up</sub>	V <sub>I2C_BUS</sub> = 1.8V +/-10%		1.6	2	2.5	kΩ
R <sub>Pull-up</sub>	V <sub>I2C_BUS</sub> = 3.3V +/-10%		2.8	4.7	7	kΩ
SCL Frequency					400	kHz
DxP, DxM	•				<u>'</u>	
C <sub>IO_DXX</sub>	Capacitance to GND	Measured with VNA at 240 MHz, V <sub>CC</sub> supply stable, Redriver off		2.5		pF

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

# **6.6 Switching Characteristics**

Over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
DxP, DxM US	SB Signals					
F <sub>BR_DXX</sub>	Bit Rate	USB channel = HS mode. 480 Mbps traffic. V <sub>CC</sub> supply stable			480	Mbps
t <sub>R/F_DXX</sub>	Rise/Fall time		100			ps

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.



# 6.7 Timing Requirements

		MIN	NOM	MAX	UNIT
POWER U	P TIMING			-	
T <sub>RSTN_PW</sub>	Minimum width to detect a valid RSTN signal assert when the pin is actively driven low	100			μs
T <sub>STABLE</sub>	VCC must be stable before RSTN de-assertion	300			μs
T <sub>READY</sub>	Maximum time needed for the device to be ready after RSTN is deasserted.			500	μs
T <sub>RAMP</sub>	V <sub>CC</sub> ramp time			100	ms
T <sub>RAMP</sub>	V <sub>CC</sub> ramp time	0.2			ms
2C (STD)				'	
t <sub>susто</sub>	Stop setup time, SCL ( $T_r$ =600ns-1000ns), SDA ( $T_f$ =6.5ns-106.5ns), 100kHz STD	4			μs
t <sub>HDSTA</sub>	Start hold time, SCL (Tr=600ns-1000ns), SDA (Tf=6.5ns-106.5ns), 100kHz STD	4			μs
t <sub>SUSTA</sub>	Start setup time, SCL (T <sub>r</sub> =600ns-1000ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 100kHz STD	4.7			μs
t <sub>SUDAT</sub>	Data input or False start/stop, setup time, SCL (T <sub>r</sub> =600ns-1000ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 100kHz STD	250			ns
t <sub>HDDAT</sub>	Data input or False start/stop, hold time, SCL (T <sub>r</sub> =600ns-1000ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 100kHz STD	5			μs
t <sub>BUF</sub>	Bus free time between START and STOP conditions	4.7			μs
t <sub>LOW</sub>	Low period of the I2C clock	4.7			μs
t <sub>HIGH</sub>	High period of the I2C clock	4			μs
t <sub>F</sub>	Fall time of both SDA and SCL signals			300	ns
t <sub>R</sub>	Rise time of both SDA and SCL signals			1000	ns
I2C (FM)					
t <sub>susto</sub>	Stop setup time, SCL (T <sub>r</sub> =180ns-300ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 400 kHz FM	0.6			μs
t <sub>HDSTA</sub>	Start hold time, SCL (T <sub>r</sub> =180ns-300ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 400 kHz FM	0.6			μs
t <sub>SUSTA</sub>	Start setup time, SCL (T <sub>r</sub> =180ns-300ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 400 kHz FM	0.6			μs
t <sub>SUDAT</sub>	Data input or False start/stop, setup time, SCL (T <sub>r</sub> =180ns-300ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 400 kHz FM	100			ns
t <sub>HDDAT</sub>	Data input or False start/stop, hold time, SCL (T <sub>r</sub> =180ns-300ns), SDA (T <sub>f</sub> =6.5ns-106.5ns), 400 kHz FM	0			μs
BUF	Bus free time between START and STOP conditions	1.3			μs
t <sub>LOW</sub>	Low period of the I2C clock	1.3			μs
t <sub>HIGH</sub>	High period of the I2C clock	0.6			μs
t <sub>F</sub>	Fall time of both SDA and SCL signals			300	ns
t <sub>R</sub>	Rise time of both SDA and SCL signals			300	ns

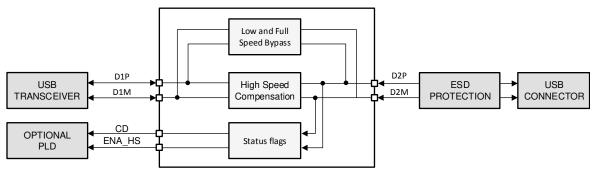
### 7 Detailed Description

#### 7.1 Overview

The TUSB216I is a USB High-Speed (HS) signal conditioner designed to compensate for ISI signal loss in a transmission channel. TUSB216I has a patented design for USB Low Speed (LS) and Full Speed (FS) signals. It does not alter the signal characteristics. HS signals are compensated. The design is compatible with USB On-The-Go (OTG) and Battery Charging (BC) specifications.

Programmable signal gain through an external resistor permits fine tuning device performance to optimize signals. This helps pass USB HS electrical compliance tests at the connector. Additional RX sensitivity, tuned by external pull-up resistor and pull-down resistor, allows to overcome attenuation in cables. The TUSB216I allows application in series to cover longer distances, or high loss transmission paths. A maximum of 4 devices can be daisy-chained.

#### 7.2 Functional Block Diagram



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### 7.3 Feature Description

#### 7.3.1 High-Speed Boost

The high-speed booster (combination of edge boost and DC boost) improves the eye width for USB2.0 high-speed signals. It is direction independent and by that is compatible to OTG systems. The BOOST pin is configuring the booster strength with different values of pull down resistors to set 4 levels of boosts, alternatively the boost level can be set through the I2C register according to \$\frac{1}{2}\sumsymbol{2} > 7.4.6\$. Internal circuitry of the signal conditioner reduces possible overshoot.

#### 7.3.2 RX Sensitivity

The RX\_SEN pin is a tri-level pin. It is used to set the gain of the device according to system channel loss. RX sensitivity can be increased to recover incoming signals with low vertical eye opening to be able to boost weak signals and helps overcoming high attenuation.

#### 7.4 Device Functional Modes

#### 7.4.1 Low-Speed (LS) Mode

TUSB216I automatically detects a LS connection and does not enable signal compensation. CD pin is asserted high but ENA\_HS will be low.

#### 7.4.2 Full-Speed (FS) Mode

TUSB216I automatically detects a FS connection and does not enable signal compensation. CD pin is asserted high but ENA\_HS will be low

#### 7.4.3 High-Speed (HS) Mode

TUSB216I automatically detects a HS connection and will enable signal compensation as determined by the configuration of the RX\_SEN pin and the external pull down resistance on its BOOST pin.

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CD pin and ENA HS pin are asserted high when high-speed boost is active.

#### 7.4.4 High-Speed Downstream Port Electrical Compliance Test Mode

TUSB216I will detect HS compliance test fixture and enter downstream port high-speed eye diagram test mode. CD pin will be low and ENA\_HS pin is asserted high when TUSB216I is in HS eye compliance test mode.

If RSTN pin is asserted low and de-asserted high while TUSB216I is operating in HS functional mode, TUSB216I will transition to HS eye compliance test mode and CD asserts low and ENA\_HS remains high. When this occurs signal compensation is enabled.

#### 7.4.5 Shutdown Mode

TUSB216I can be disabled when its RSTN pin is asserted low. DP, DM traces are continuous through the device in shutdown mode. The USB channel is still fully operational, but there is neither signal compensation, nor any indication from the CD pin as to the status of the channel.

2. Il ob alla zivizito i illo ili billotto il illotto						
MODE	CD	ENA_HS				
Low-speed	HIGH	LOW				
Full-speed	HIGH	LOW				
High-speed	HIGH	HIGH				
High-speed downstream port electrical test	LOW	HIGH				
Shutdown	LOW	LOW				

表 7-1. CD and ENA\_HS Pins in Different Modes

#### 7.4.6 I<sup>2</sup>C Mode

TUSB216I supports 100 and 400 kHz I2C for device configuration, status read back and test purposes. For detail electrical and functional specifications refer to I2C Bus Specification – STANDARD and FAST MODE. This controller is enabled after SCL and SDA pins are sampled high shortly after return from shutdown. In this mode, the CSR can be accessed by I2C read/write transaction to 7-bit slave address 0x2C. It is advised to set CFG\_ACTIVE bit before changing values. This halts the FSM, and reset it after all changes are made. This ensure proper startup into high-speed mode.

#### 7.4.7 BC 1.2 Battery Charging Controller

The TUSB216I main function is a signal conditioner offering the boost and pre-equalization features to the incoming DP/DM signals. For applications in which USB host or hub does not provide USB BC charging controller functionality, the TUSB216I can perform this task when CDP\_ENZ is low and BC 1.2 CDP Controller is enabled. When battery charging CDP controller feature is enabled (CDP\_ENZ=low) TUSB216I supports CDP charging downstream port functionality. CDP\_ENZ has an internal pull up when the pin is left unconnected CDP controller will be disabled.

表 7-2. TUSB216I Battery Charging Controller Modes

Pin 11 (CDP_ENZ)	CDP
High	NO
Low	YES

#### 7.5 TUSB216 Registers

表 7-3 lists the memory-mapped registers for the TUSB216 registers. All register offset addresses not listed in 表 7-3 should be considered as reserved locations and the register contents should not be modified.

表 7-3. TUSB216 Registers

Offset	Acronym	Register Name	Section
0x1	EDGE_BOOST	This register is setting EDGE BOOST level.	Go
0x3	CONFIGURATION	This register is selecting device mode.	Go

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### 表 7-3. TUSB216 Registers (続き)

Offset	Acronym	Register Name	Section
0xE	DC_BOOST	This register is setting DC BOOST level.	Go
0x25	RX_SEN	This register is setting RX Sensitivity level.	Go

Complex bit access types are encoded to fit into small table cells.  $\frac{1}{2}$  7-4 shows the codes that are used for access types in this section.

表 7-4. TUSB216 Access Type Codes

22 7-4: 100B210 Access Type Codes					
Access Type	Access Type Code Description				
Read Type					
RH H Set or cleared by hardware Read					
Write Type					
W	W	Write			
Reset or Default	Reset or Default Value				
-n	Value after reset or the default value				

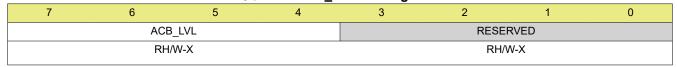
#### 7.5.1 EDGE\_BOOST Register (Offset = 0x1) [reset = X]

EDGE\_BOOST is shown in 図 7-1 and described in 表 7-5.

Return to Summary Table.

This register is setting EDGE BOOST level.

# 図 7-1. EDGE\_BOOST Register



## 表 7-5. EDGE\_BOOST Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	ACB_LVL	RH/W	Х	XXXXb (sampled at startup from BOOST pin)
				0000b to 1111b range
				0x0 = BOOST PIN LEVEL 0 (lowest edge boost setting)
				0x3 = BOOST PIN LEVEL 1
				0x6 = BOOST PIN LEVEL 2
				0xA = BOOST PIN LEVEL 3
				0xF = (highest edge boost setting)
3-0	RESERVED	RH/W	Х	These bits are reserved bits and set by hardware at reset.
				When this register is modified the software should first read these
				reserved bits and rewrite with the same values

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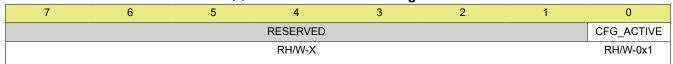
### 7.5.2 CONFIGURATION Register (Offset = 0x3) [reset = X]

CONFIGURATION is shown in  $\boxtimes$  7-2 and described in  $\not\equiv$  7-6.

Return to Summary Table.

This register is selecting device mode.

# 図 7-2. CONFIGURATION Register



### 表 7-6. CONFIGURATION Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-1	RESERVED	RH/W	Х	These bits are reserved bits and set by hardware at reset.  When this register is modified the software should first read these reserved bits and rewrite with the same values
0	CFG_ACTIVE	RH/W	0x1	Configuration mode After reset, if I2C mode is true (SCL and SDA are both pulled high) set the bit to get into configuration mode and clear to return to normal mode.  0x0 = NORMAL MODE  0x1 = CONFIGURATION MODE

### 7.5.3 DC\_BOOST Register (Offset = 0xE) [reset = X]

DC\_BOOST is shown in  $\boxtimes$  7-3 and described in  $\not\equiv$  7-7.

Return to Summary Table.

This register is setting DC BOOST level.

#### 図 7-3. DC\_BOOST Register



#### 表 7-7. DC\_BOOST Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	RESERVED	RH/W	Х	These bits are reserved bits and set by hardware at reset.  When this register is modified the software should first read these reserved bits and rewrite with the same values
3-0	DCB_LVL	RH/W	X	XXXXb (sampled at startup from BOOST pin) 0000b to 1111b range  0x0 = BOOST PIN LEVEL 0 (lowest dc boost setting)  0x2 = BOOST PIN LEVEL 1 and 2  0x6 = BOOST PIN LEVEL 3  0xF = (highest dc boost setting)

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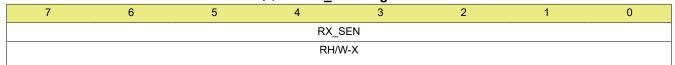
# 7.5.4 RX\_SEN Register (Offset = 0x25) [reset = X]

RX\_SEN is shown in 図 7-4 and described in 表 7-8.

Return to Summary Table.

This register is setting RX Sensitivity level.

### 図 7-4. RX\_SEN Register



### 表 7-8. RX\_SEN Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-0	RX_SEN	RH/W		XXXXb (sampled at startup from RX_SEN pin) 00000000b to 11111111b range  0x0 = RX_SEN LEVEL LOW  0x33 = RX SEN LEVEL MID
				0x66 = RX_SEN LEVEL HIGH 0xFF = (highest setting)



### 8 Application and Implementation

注

以下のアプリケーション情報は、TIの製品仕様に含まれるものではなく、TIではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

#### 8.1 Application Information

The purpose of the TUSB216I is to re-store the signal integrity of a USB High-speed channel up to the USB connector. The loss in signal quality stems from reduced channel bandwidth due to high loss PCB trace and other components that contribute a capacitive load. This can cause the channel to fail the USB near end eye mask. Proper use of the TUSB216I can help to pass this eye mask.

A secondary purpose is to use the CD pin of the TUSB216I to control other blocks on the customer platform, if so desired.

#### 8.2 Typical Application

A typical application for TUSB216I is shown in 🗵 8-1. In this setup, D2P and D2M face the USB connector while D1P and D1M face the USB host. The orientation may be reversed [that is, D2 faces transceiver and D1 faces connector].

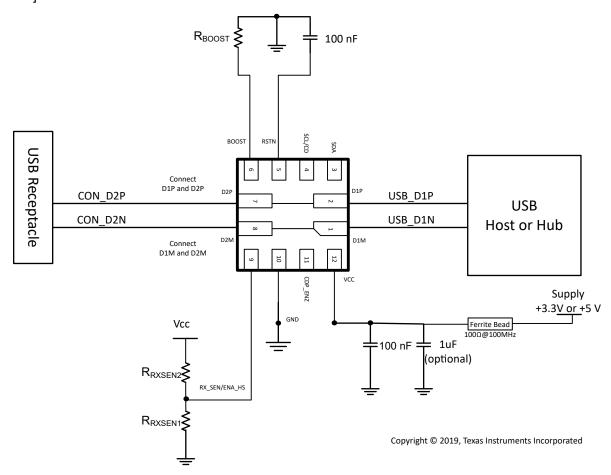


図 8-1. TUSB216I Reference Schematic (Design Example with CDP disabled), CDP\_ENZ Can Be Left Floating but an Option for a Decoupling Capacitor of 0.1 μF is Recommended So the Design is Compatible with Older Devices: TUSB211, TUSB212, TUSB214

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### 8.2.1 Design Requirements

TUSB216I requires a valid reset signal as described in the *Power Supply Recommendations* section. The capacitor at RSTN pin is not required if a micro controller drives the RSTN pin according to recommendations.

For this design example, use the parameters shown in 表 8-1, 表 8-2 and 表 8-3.

表 8-1. Design Parameters for 5-V Supply With High Loss System

	<b>200</b> 11 2 001911 1 11111110	ters for a v cuppiy vitti ii		
	VALUE <sup>(1)</sup>			
V <sub>CC</sub>		5 V ±10%		
I <sup>2</sup> C support require	No			
		R <sub>BOOST</sub>	BOOST Level	
		0-Ω	0	
Edge and DC Boost		1.8 kΩ ±1%	1	Boost Level 1: $R_{BOOST} = 1.8 \text{ k}\Omega$
		3.6 kΩ ± 1%	2	1,80021 1.0 1/22
Do Not Install (DNI)				
	R <sub>RXSEN1</sub> R <sub>RXSEN2</sub>		RX_SEN Level	High RX
	22 kΩ - 40 kΩ (27 kΩ typical)	Do Not Install (DNI)	Low	Sensitivity Level: R <sub>RXSEN1</sub> = 37.5
RX Sensitivity	Do Not Install (DNI)	Do Not Install (DNI)	Medium	$k\Omega$
	37.5 kΩ <sup>(2)</sup>	12.5 kΩ	High	$R_{RXSEN2} = 12.5$ $k\Omega$

<sup>(1)</sup> These parameters are starting values for a high loss system. Further tuning might be required based on specific host or device as well as cable length and loss profile. These settings are not specific to a 5 V supply system could be applicable to 3.3 V supply system as well.

表 8-2. Design Parameters for 3.3-V Supply With Low to Medium Loss System

PARAMETER								
V <sub>CC</sub>								
I <sup>2</sup> C support require	I <sup>2</sup> C support required in system (Yes/No)							
		R <sub>BOOST</sub>	BOOST Level					
	0-Ω 0 DC Boost 1.8 kΩ ±1% 1							
Edge and DC Boos			1	Boost Level 0: $R_{BOOST} = 0-\Omega$				
		3.6 kΩ ±1% 2  Do Not Install (DNI) 3		- 1,80031 0 22				
	R <sub>RXSEN1</sub>	R <sub>RXSEN2</sub>	RX_SEN Level	Medium RX				
RX Sensitivity	22 kΩ – 40 kΩ (27 kΩ typical)	Do Not Install (DNI)	Low	Sensitivity Level:				
	Do Not Install (DNI)	Do Not Install (DNI)	Medium	R <sub>RXSEN1</sub> = DNI				
	Do Not Install (DNI)	22 kΩ – 40 kΩ (27 kΩ typical)	High	$ R_{RXSEN2} = DNI$				

<sup>(1)</sup> These parameters are starting values for a low to medium loss system. Further tuning might be required based on specific host or device as well as cable length and loss profile. These settings are not specific to a 3.3 V supply system could be applicable to 5 V supply system as well.

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<sup>(2)</sup> This resistor is needed for a 5 V supply to divide the voltage down so the RX\_SEN pin voltage does not exceed 5.0 V.



### 表 8-3. Design Parameters for 2.3-V to 4.3-V VBAT Supply With Low to Medium Loss System

PARAMETER								
V <sub>CC</sub>								
I <sup>2</sup> C support require	I <sup>2</sup> C support required in system (Yes/No)							
		R <sub>BOOST</sub>	BOOST Level					
	0-Ω		0	1				
Edge and DC Boo	st	1.8 kΩ ±1%	1	Boost Level 0: $R_{BOOST} = 0-\Omega$				
		3.6 kΩ ±1%	2	- 10031 0 11				
	Do Not Install (DNI)		3					
	R <sub>RXSEN1</sub>	R <sub>RXSEN2</sub>	RX_SEN Level	Medium RX				
RX Sensitivity	22 kΩ – 40 kΩ (27 kΩ typical)	Do Not Install (DNI)	Low	Sensitivity Level:				
	Do Not Install (DNI)	Do Not Install (DNI)	Medium	R <sub>RXSEN1</sub> = DNI				
	37.5 kΩ <sup>(2)</sup>	12.5 kΩ	High	$R_{RXSEN2} = DNI$				

<sup>(1)</sup> These parameters are starting values for a low to medium loss system. Further tuning might be required based on specific host or device as well as cable length and loss profile. These settings are not specific to a 2.3 V – 4.3 V supply system could be applicable to 5 V supply system as well.

#### 8.2.2 Detailed Design Procedure

The ideal BOOST setting is dependent upon the signal chain loss characteristics of the target platform. The recommendation is to start with BOOST level 0, and then increment to BOOST level 1, and so on. Same applies to the RX sensitivity setting where it is recommended to plan for the required pads or connections to change boost settings, but to start with RX sensitivity level Low.

In order for the TUSB216I to recognize any change to the BOOST setting, the RSTN pin must be toggled. This is because the BOOST pin is latched on power up and the pin is ignored thereafter.

注

The TUSB216I compensates for extra attenuation in the signal path according to the configuration of the RX\_SEN pin. This maximum recommended voltage for this pin is 5 V when selecting the highest RX sensitivity level.

Placement of the device is also dependent on the application goal. 表 8-4 summarizes our recommendations.

#### 表 8-4. Platform Placement Guideline

PLATFORM GOAL	SUGGESTED TUSB216I PLACEMENT
Pass USB Near End Mask at the receptacle	Close to measurement point (connector)
Pass USB Far End Eye Mask at the plug	Close to USB PHY
Cascade multiple TUSB216Is to improve device enumeration	Midway between each USB interconnect

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<sup>(2)</sup> This resistor is needed for a VBAT supply (2.3 V – 4.3 V) to divide the voltage down so the RX\_SEN pin voltage does not exceed 5.0 V.

# 表 8-5. Table of Recommended Settings

at our rabio of recommended contingo								
BOOST and RX_SEN settings (1) for channel loss								
Pre-channel cable length (Between USB PHY and TUSB216I)	BOOST	RX_SEN						
0-3 meter	Level 0	Medium or High						
2-5 meter	Level 1	Medium or High						
Post-channel cable length (Between TUSB216l and inter-connect)	BOOST	RX_SEN						
0-2 meter	Level 0	Medium or High						
1-4 meter	Level 1	Medium or High						

<sup>(1)</sup> These parameters are starting values for different cable lengths. Further tuning might be required based on specific host or device as well as cable length and loss profile.

#### 8.2.2.1 Test Procedure to Construct USB High-speed Eye Diagram

注

USB-IF certification tests for High-speed eye masks require the *mandated use* of the USB-IF developed test fixtures. These test fixtures do not require the use of oscilloscope probes. Instead they use SMA cables. More information can be found at the USB-IF Compliance Updates Page. It is located under the *Electrical Specifications* section, ID 86 dated March 2013.

The following procedure must be followed before using any oscilloscope compliance software to construct a USB High-speed Eye Mask:

#### 8.2.2.1.1 For a Host Side Application

- 1. Configure the TUSB216I to the desired BOOST setting
- 2. Power on (or toggle the RSTN pin if already powered on) the TUSB216I
- 3. Using SMA cables, connect the oscilloscope and the USB-IF host-side test fixture to the TUSB216I
- Enable the host to transmit USB TEST PACKET
- 5. Execute the oscilloscope USB compliance software.
- 6. Repeat the above steps in order to re-test TUSB216I with a different BOOST setting (must reset to change)

#### 8.2.2.1.2 For a Device Side Application

- 1. Configure the TUSB216I to the desired BOOST setting
- 2. Power on (or toggle the RSTN pin if already powered on) the TUSB216I
- 3. Connect a USB host, the USB-IF device-side test fixture, and USB device to the TUSB216I. Ensure that the USB-IF device test fixture is configured to the 'INIT' position
- 4. Allow the host to enumerate the device
- 5. Enable the device to transmit USB TEST PACKET
- 6. Using SMA cables, connect the oscilloscope to the USB-IF device-side test fixture and ensure that the device-side test fixture is configured to the 'TEST' position.
- 7. Execute the oscilloscope USB compliance software.
- 8. Repeat the above steps in order to re-test TUSB216I with a different BOOST setting (must reset to change)

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### 8.2.3 Application Curves

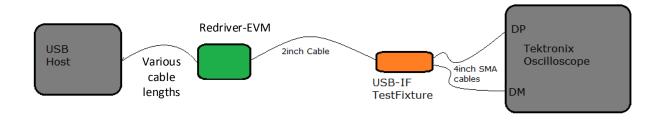
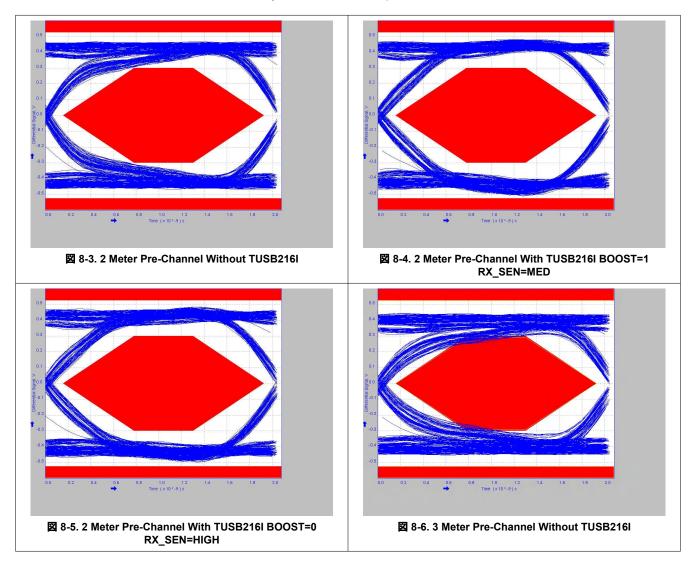


図 8-2. Near End Eye Measurement Set-Up With Pre-Channel Cable



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### 8.2.3 Application Curves (continued)

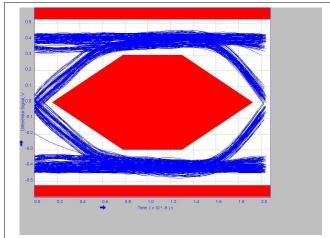


図 8-7. 3 Meter Pre-Channel With TUSB216I BOOST=0 RX\_SEN=HIGH

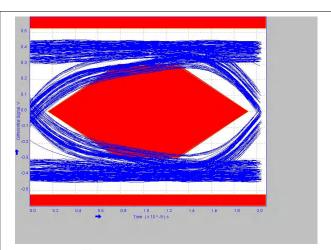


図 8-8. 5 Meter Without TUSB216I

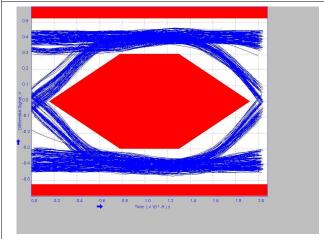


図 8-9. 5 Meter Pre-Channel With TUSB216I BOOST=1 RX\_SEN=MED

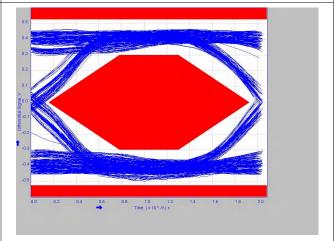


図 8-10. 5 Meter Pre-Channel With TUSB216I BOOST=2 RX\_SEN=MED



### 8.2.3 Application Curves

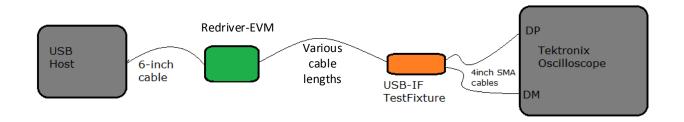
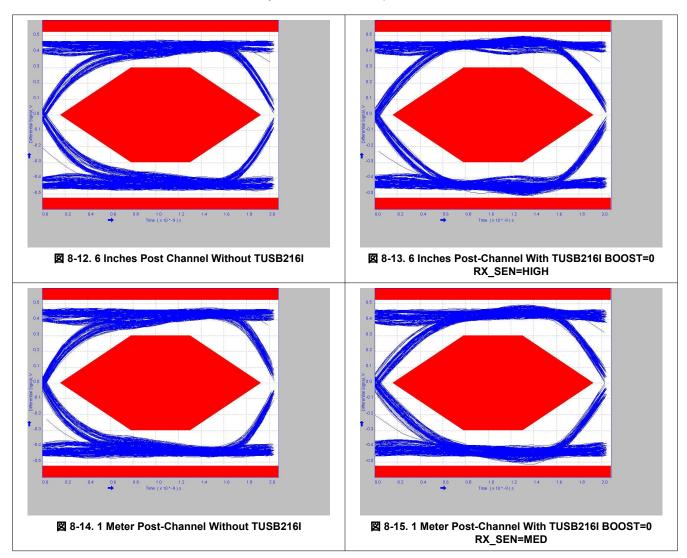


図 8-11. Near End Eye Measurement Set-Up With Post-Channel Cable



### 8.2.3 Application Curves (continued)

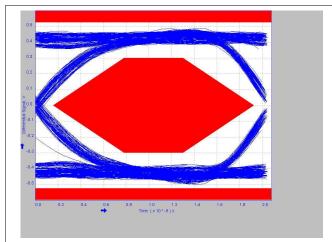


図 8-16. 1 Meter Post-Channel With TUSB216I BOOST=0 RX\_SEN=HIGH

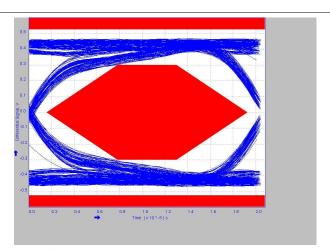


図 8-17. 2 Meter Post-Channel Without TUSB216I

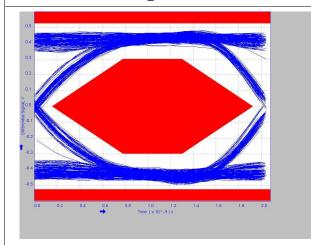


図 8-18. 2 Meter Post-Channel With TUSB216I BOOST=1 RX\_SEN=MED

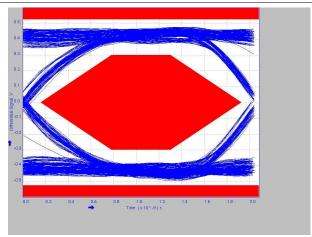


図 8-19. 2 Meter Post-Channel With TUSB216I BOOST=1 RX\_SEN=HIGH

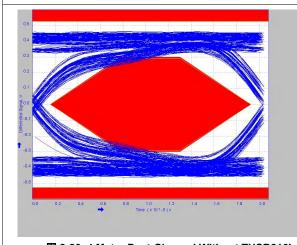


図 8-20. 4 Meter Post-Channel Without TUSB216I

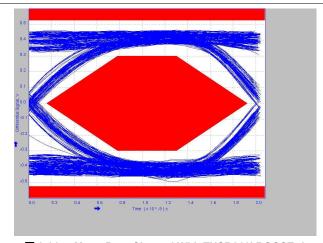


図 8-21. 4 Meter Post-Channel With TUSB216I BOOST=2
RX\_SEN=MED



#### 8.3 Power Supply Recommendations

On power up, the interaction of the RSTN pin and power on ramp could result in digital circuits not being set correctly. The device should not be enabled until the power on ramp has settled to minimum recommended supply voltage or higher to ensure a correct power on reset of the digital circuitry. If RSTN cannot be held low by microcontroller or other circuitry until the power on ramp has settled, then an external capacitor from the RSTN pin to GND is required to hold the device in the low power reset state.

The RC time constant should be larger than five times of the power on ramp time (0 to  $V_{CC}$ ). With a typical internal pullup resistance of 500 k $\Omega$ , the recommended minimum external capacitance is calculated as:

[Ramp Time x 5] ÷ [500 k
$$\Omega$$
] (1)

### 8.4 Layout

### 8.4.1 Layout Guidelines

Although the land pattern has matched trace width to pad width, optimal impedance control is based on the user's own PCB stack-up. The recommendation is to maintain  $90 \Omega$  differential routing underneath the device.

# 8.4.2 Layout Example

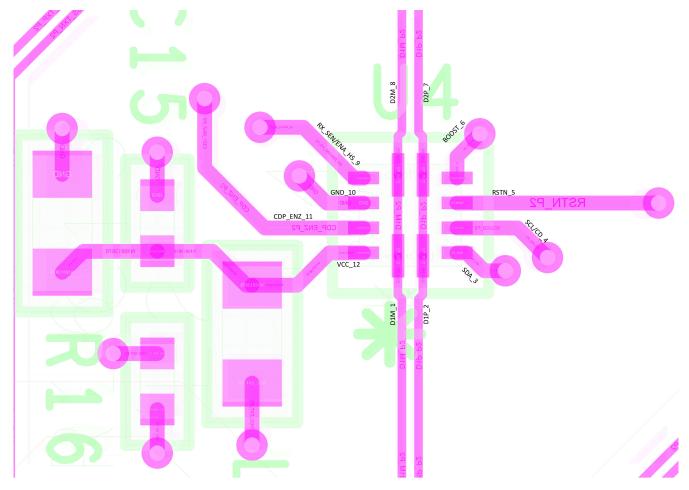


図 8-22. Layout Example

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# 9 Device and Documentation Support

### 9.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

#### 9.2 サポート・リソース

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リンクされているコンテンツは、各寄稿者により「現状のまま」提供されるものです。これらはテキサス・インスツルメンツの仕様を構成するものではなく、必ずしもテキサス・インスツルメンツの見解を反映したものではありません。テキサス・インスツルメンツの使用条件を参照してください。

#### 9.3 Trademarks

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#### 9.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

#### 9.5 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

# 10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

CI	hanges from Revision * (March 2021) to Revision A (December 2023)	Page
•	Added Device Comparison section	2
	Added 400 kHz I2C support	
	Added timing table for 400 kHz I2C Fast Mode	
•	Added I2C standard and fast mode support in Detailed Description	10

#### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: TUSB2161

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資料に関するフィードバック(ご意見やお問い合わせ)を送信

www.ti.com 9-Nov-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
TUSB216IRWBR	Active	Production	X2QFN (RWB)   12	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	61
TUSB216IRWBR.A	Active	Production	X2QFN (RWB)   12	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	61
TUSB216IRWBT	Active	Production	X2QFN (RWB)   12	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	61
TUSB216IRWBT.A	Active	Production	X2QFN (RWB)   12	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	61

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

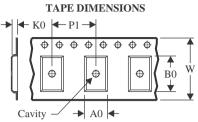
<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

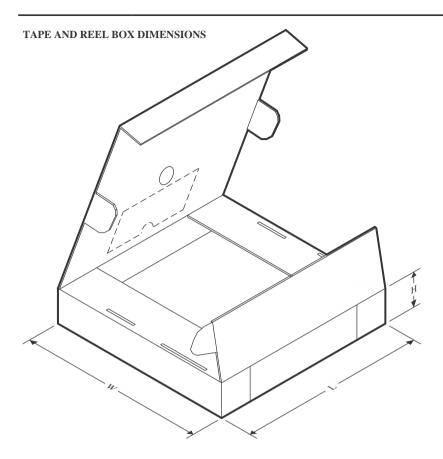
#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TUSB216IRWBR	X2QFN	RWB	12	3000	180.0	9.5	1.8	1.8	0.45	4.0	8.0	Q1
TUSB216IRWBT	X2QFN	RWB	12	250	180.0	9.5	1.8	1.8	0.45	4.0	8.0	Q1

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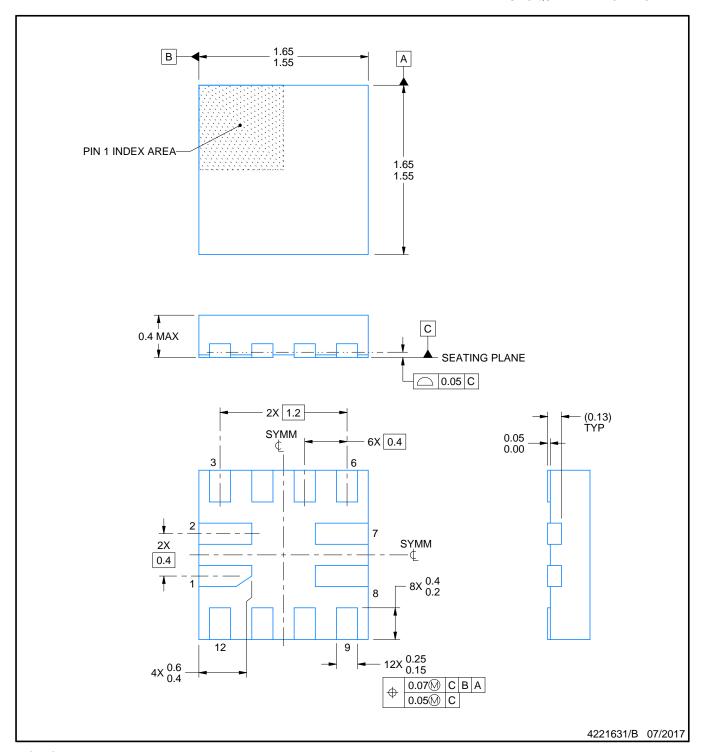


#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TUSB216IRWBR	X2QFN	RWB	12	3000	189.0	185.0	36.0
TUSB216IRWBT	X2QFN	RWB	12	250	189.0	185.0	36.0



PLASTIC QUAD FLATPACK - NO LEAD



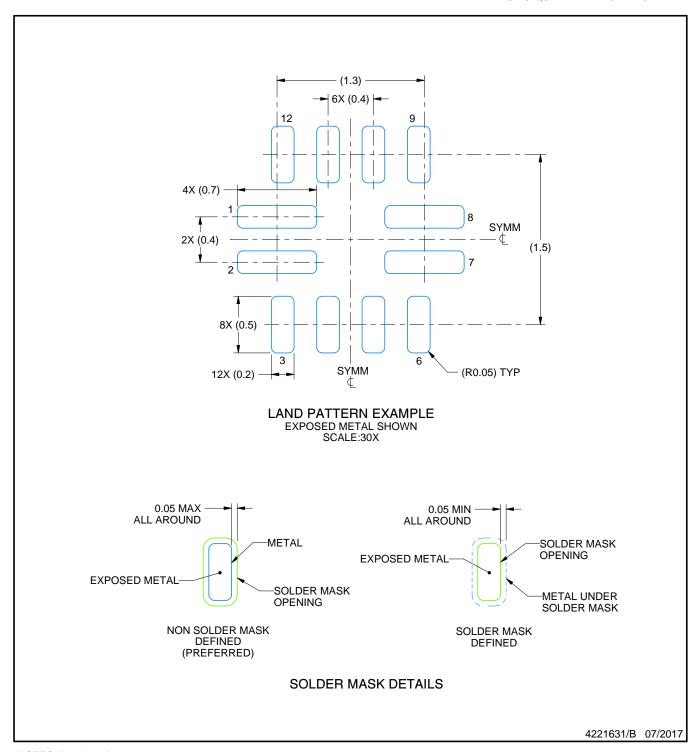
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.



PLASTIC QUAD FLATPACK - NO LEAD

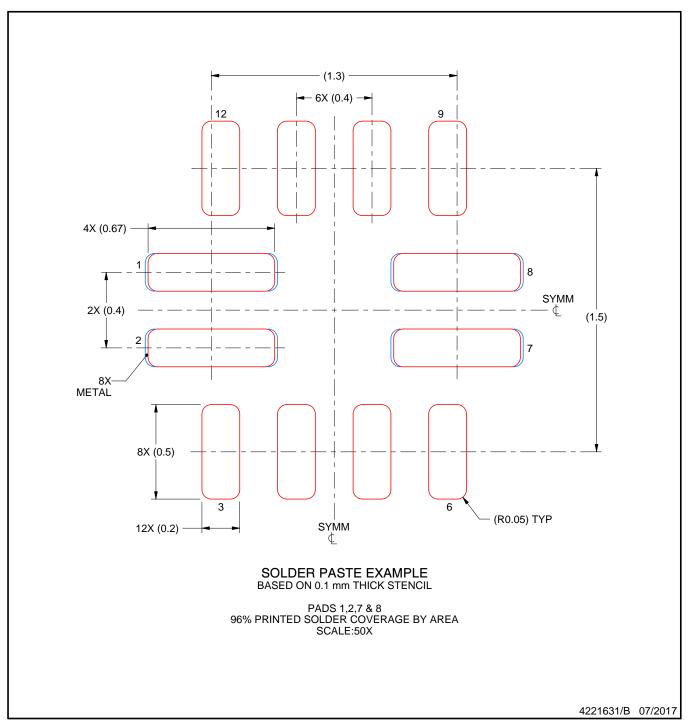


NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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